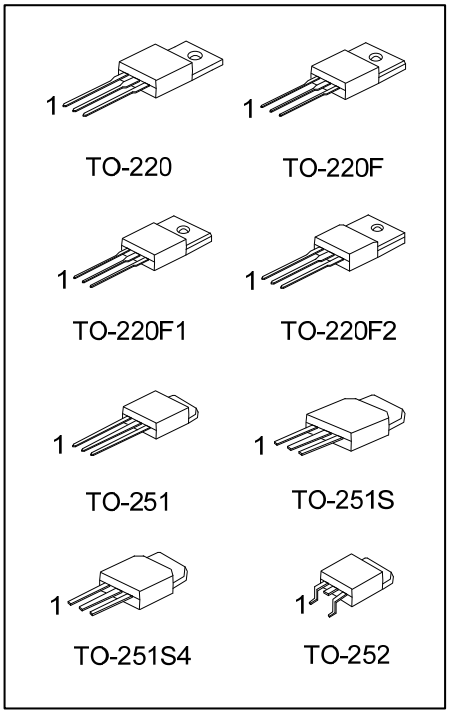
3NM80

Power MOSFET

3.0A, 800V N-CHANNEL SUPER-JUNCTION MOSFET



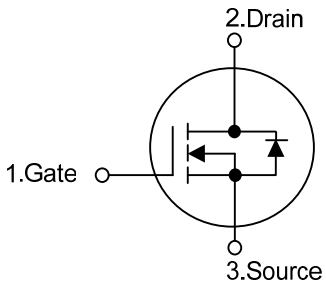
■ DESCRIPTION

The **UTC 3NM80** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

■ FEATURES

* $R_{DS(ON)} \leq 2.88\ \Omega$ @ V_{GS}=10V, I_D=1.5A
* Fast switching capability
* Avalanche energy tested
* Improved dv/dt capability, high ruggedness

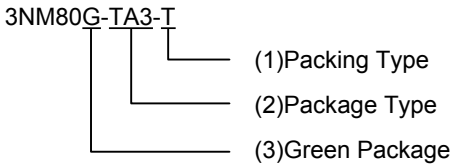
■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
3NM80L-TA3-T	3NM80G-TA3-T	TO-220	G	D	S	Tube
3NM80L-TF3-T	3NM80G-TF3-T	TO-220F	G	D	S	Tube
3NM80L-TF1-T	3NM80G-TF1-T	TO-220F1	G	D	S	Tube
3NM80L-TF2-T	3NM80G-TF2-T	TO-220F2	G	D	S	Tube
3NM80L-TM3-T	3NM80G-TM3-T	TO-251	G	D	S	Tube
3NM80L-TMS-T	3NM80G-TMS-T	TO-251S	G	D	S	Tube
3NM80L-TMS4-T	3NM80G-TMS4-T	TO-251S4	G	D	S	Tube
3NM80L-TN3-R	3NM80G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source



(1) T: Tube, R: Tape Reel
(2) TA3: TO-220, TF1: TO-220F1, TF2: TO-220F2
TF3: TO-220F, TM3: TO-251, TMS: TO-251S,
TMS4: TO-251S4, TN3: TO-252
(3) G: Halogen Free and Lead Free, L: Lead Free

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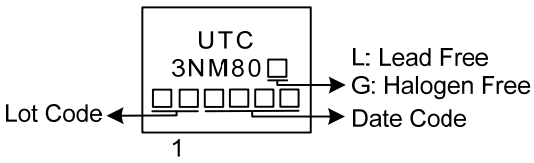
■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	800	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	3	A
	Pulsed (Note 2)	I_{DM}	6	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	100	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	1.8	V/ns
Power Dissipation	TO-220	P_D	35	W
	TO-220F/TO-220F1 TO-220F2		20	W
	TO-251/TO-251S TO-251S4/TO-252		21	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L=100mH, I_{AS}=1.4A, V_{DD}=50V, R_G=25 Ω, Starting T_J = 25°C
4. I_{SD} ≤ 3.0A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2	θ_{JA}	62.5	°C/W
	TO-251/TO-251S TO-251S4/TO-252		110	°C/W
Junction to Case	TO-220	θ_{JC}	3.57	°C/W
	TO-220F/TO-220F1 TO-220F2		6.25	°C/W
	TO-251/TO-251S TO-251S4/TO-252		5.95 (Note)	°C/W

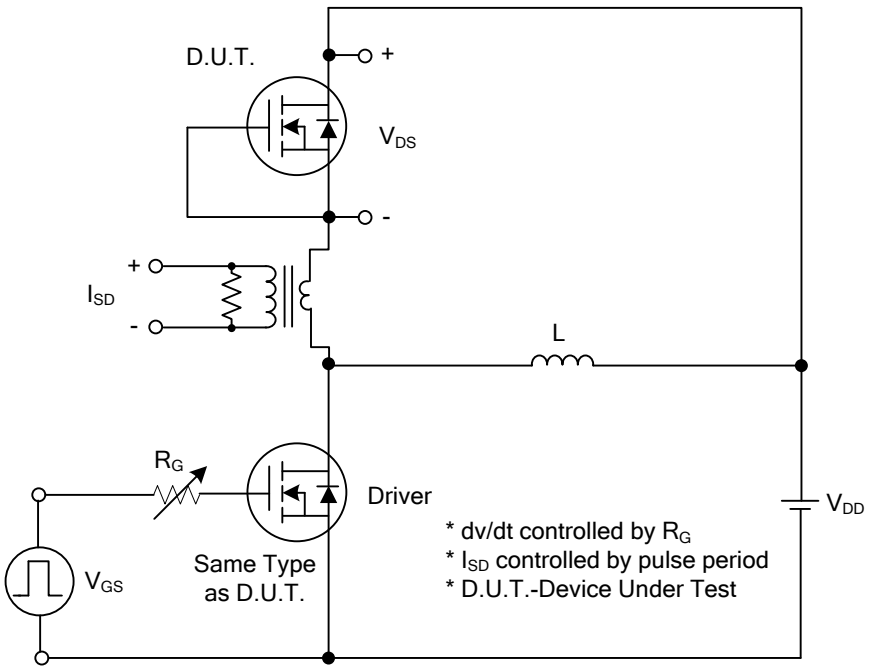
Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

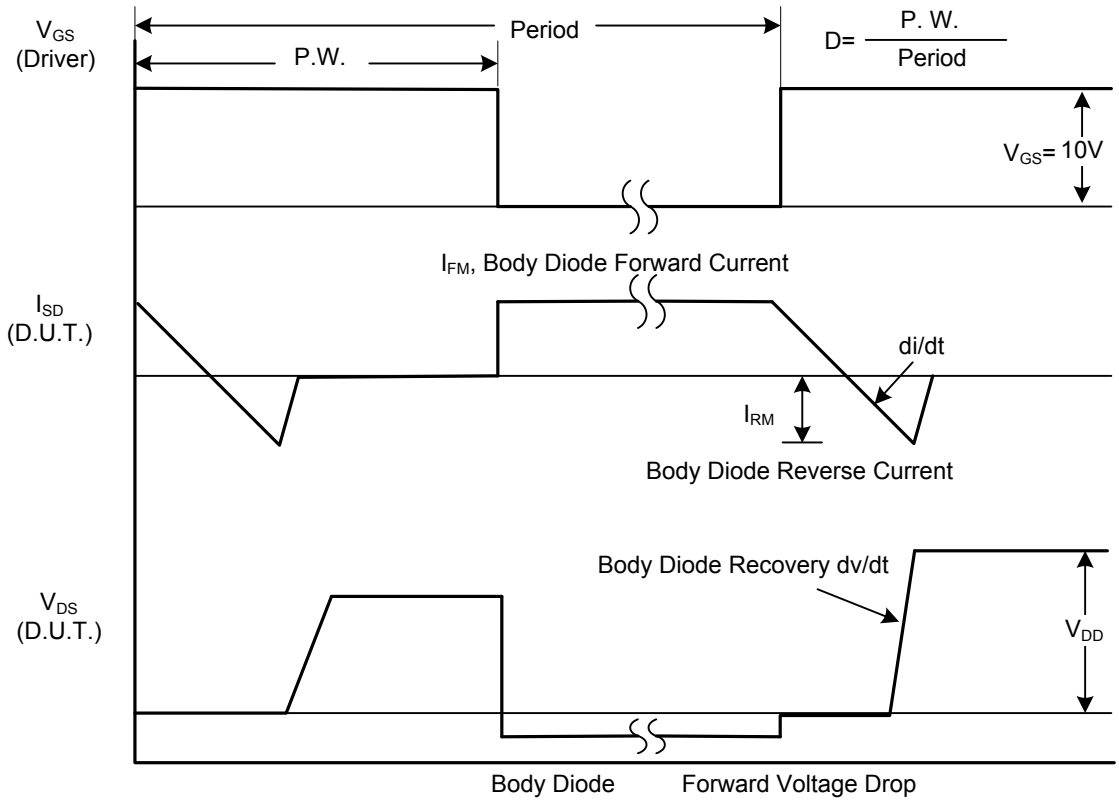
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	800			V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=800V, V_{GS}=0V			10	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=30V, V_{DS}=0V			100	nA
		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.5		4.5	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=1.5A			2.88	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	V_{GS}=0V, V_{DS}=50V, f=1.0MHz		243		pF
Output Capacitance	C_{OSS}			29.2		pF
Reverse Transfer Capacitance	C_{RSS}			2.5		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q_G	V_{DS}=640V, V_{GS}=10V, I_D=3A (Note 1,2)		18.5		nC
Gate to Source Charge	Q_{GS}			6.5		nC
Gate to Drain Charge	Q_{GD}			4		nC
Turn-ON Delay Time (Note 1)	$t_{D(ON)}$	V_{DD}=100V, V_{GS}=10V, I_D=3A, R_G=25Ω (Note 1,2)		6		nS
Rise Time	t_R			17		nS
Turn-OFF Delay Time	$t_{D(OFF)}$			31		nS
Fall-Time	t_F			29		nS
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				3	A
Maximum Body-Diode Pulsed Current	I_{SM}				6	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	I_S =3.0A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t_{rr}	I_S =3.0A, V_{GS}=0V dI$_F$/dt=100A/μs		330		nS
Body Diode Reverse Recovery Charge	Q_{rr}			2.7		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS

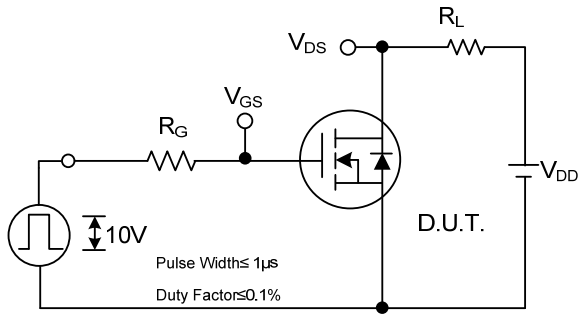


Peak Diode Recovery dv/dt Test Circuit

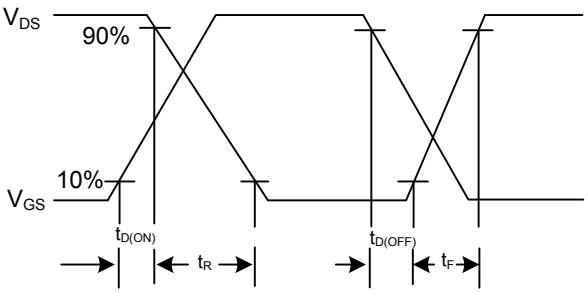


Peak Diode Recovery dv/dt Waveforms

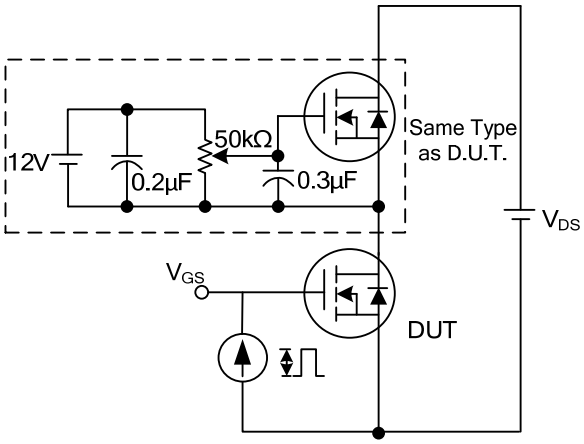
■ TEST CIRCUITS AND WAVEFORMS



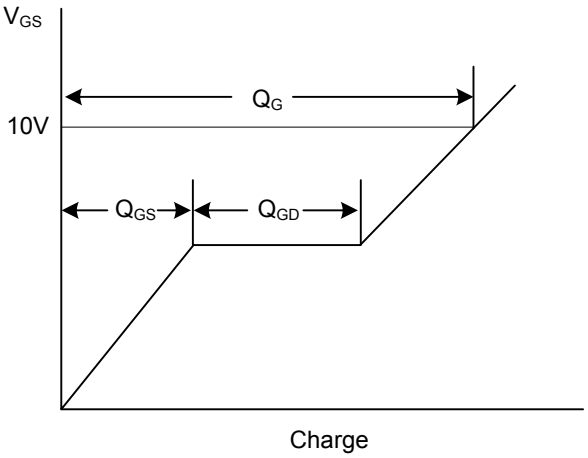
Switching Test Circuit



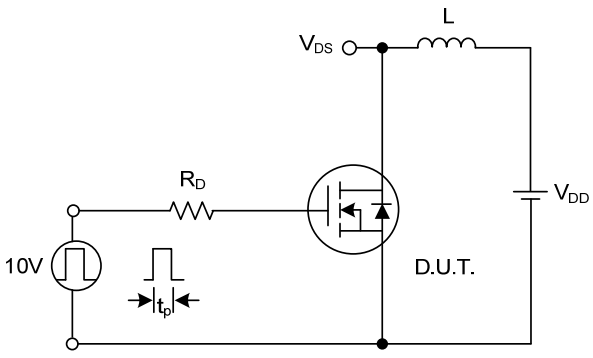
Switching Waveforms



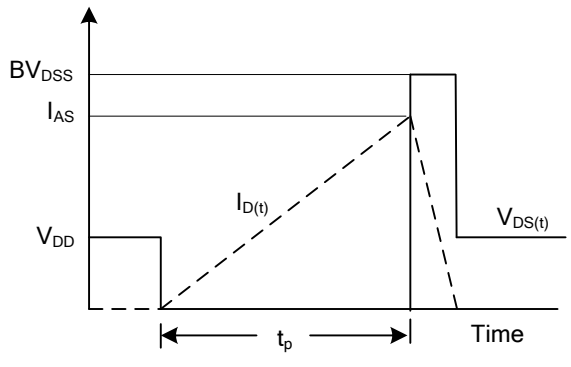
Gate Charge Test Circuit



Gate Charge Waveform



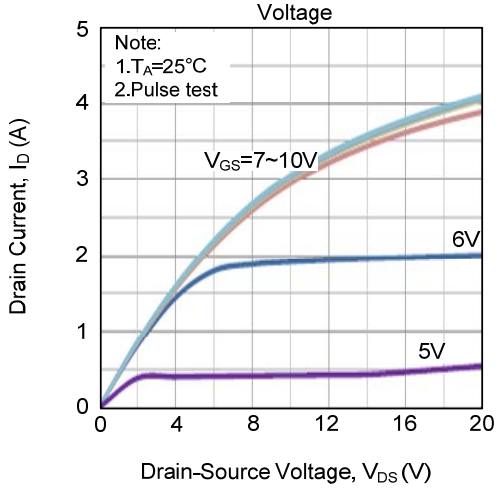
Unclamped Inductive Switching Test Circuit



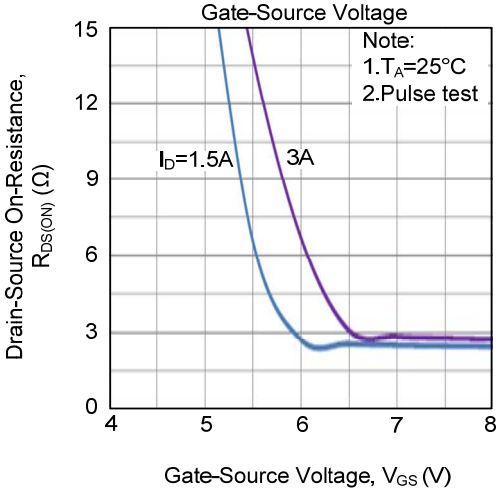
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

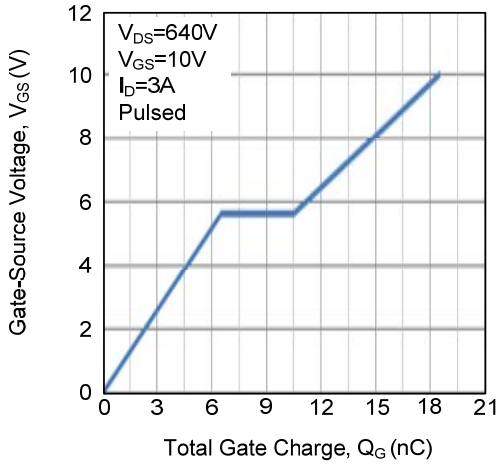
Drain Current vs. Drain-Source Voltage



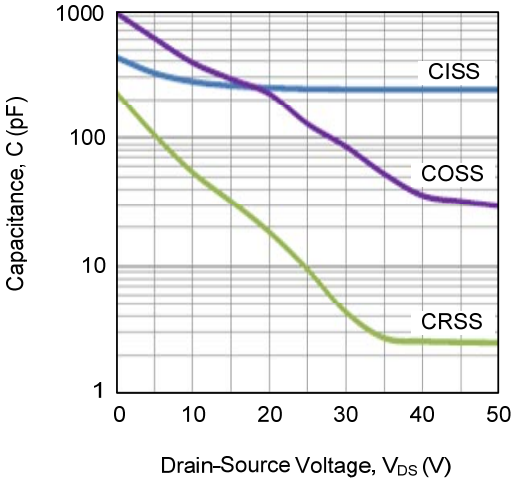
Drain-Source On-Resistance vs. Gate-Source Voltage



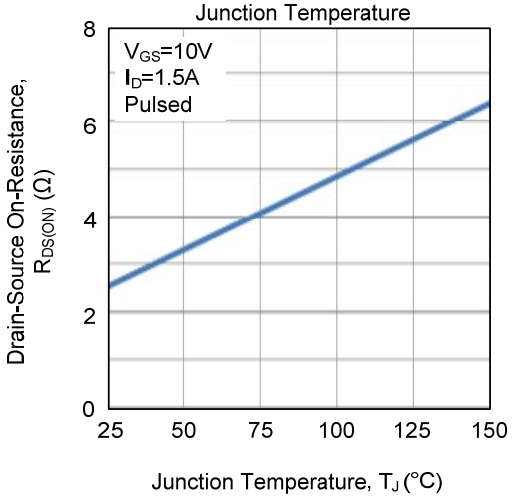
Gate Charge Characteristics



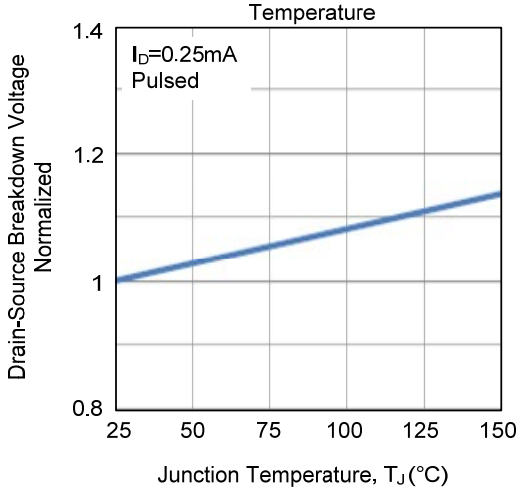
Capacitance Characteristics



Drain-Source On-Resistance vs. Junction Temperature

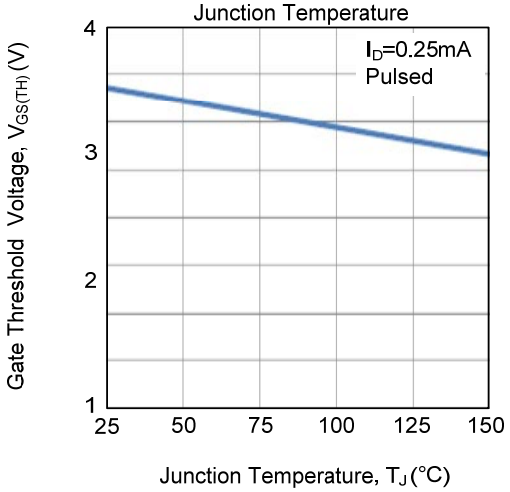


Breakdown Voltage vs. Junction Temperature

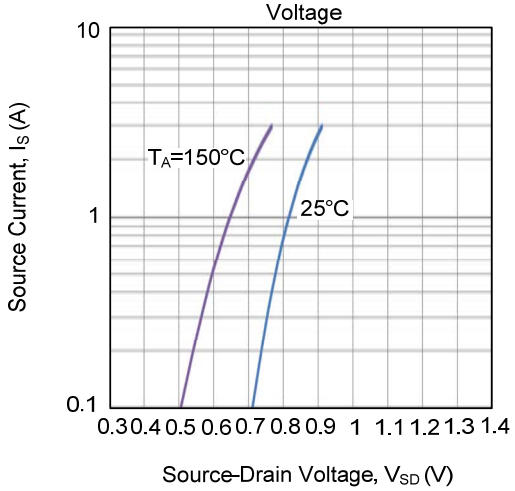


■ TYPICAL CHARACTERISTICS (Cont.)

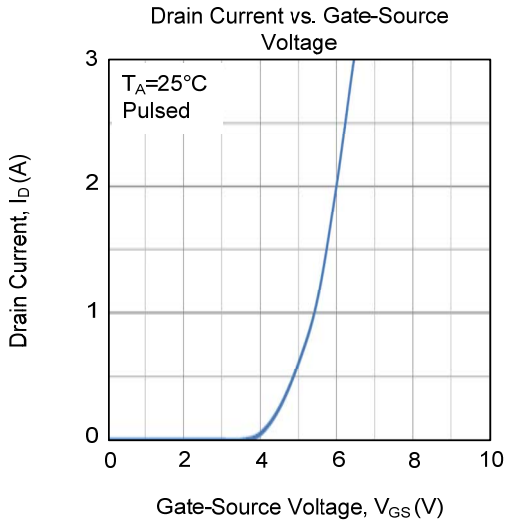
Gate Threshold Voltage vs. Junction Temperature



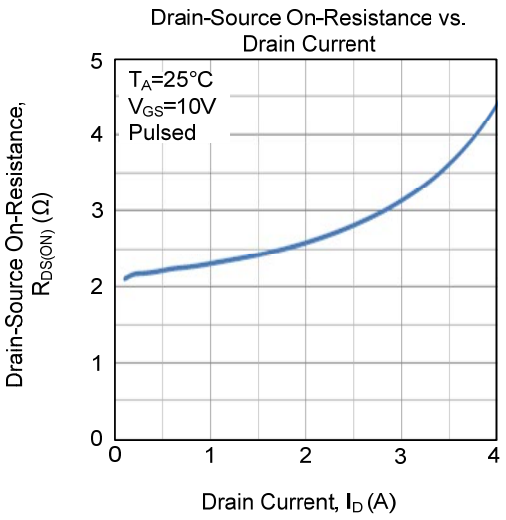
Source Current vs. Source-Drain Voltage



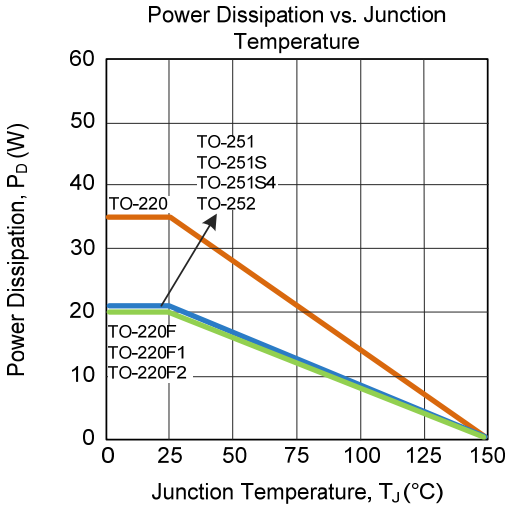
Drain Current vs. Gate-Source Voltage



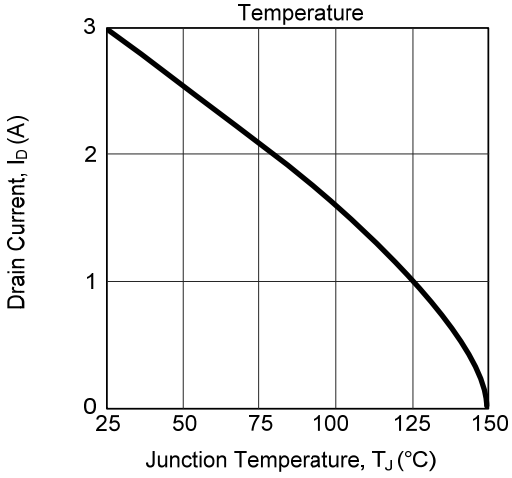
Drain-Source On-Resistance vs. Drain Current



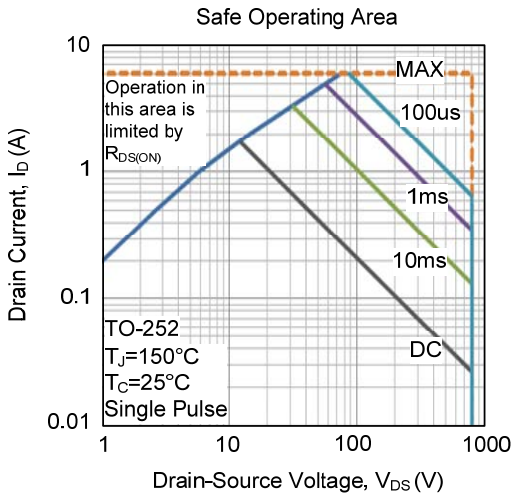
Power Dissipation vs. Junction Temperature



Drain Current vs. Junction Temperature



■ TYPICAL CHARACTERISTICS (Cont.)



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